# TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

## **FEATURES**

#### n HIGH POWER

P1dB=33.0dBm at 7.1GHz to 8.5GHz

n HIGH GAIN

G1dB=28.0dB at 7.1GHz to 8.5GHz

MICROWAVE POWER MMIC AMPLIFIER TMD7185-2

#### **n** BROAD BAND INTERNALLY MATCHED

#### n HERMETICALLY SEALED PACKAGE

## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	10
Flange Temperature	Tf	٥C	-30 ~ +80
Storage Temperature	T <sub>stg</sub>	°C	-65 ~ +175

## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	32.0	33.0	
Compression Point		VDD= 10V				
Power Gain at 1dB Gain	G1dB	VGG= -5V	dB	27.0	28.0	
Compression Point						
Drain Current	IDD	f = 7.1 – 8.5GHz	А		1.4	1.7
Input VSWR	VSWRin					3.0
3 <sup>rd</sup> Order Intermodulation	IM <sub>3</sub>	Po (S.C.L.)=22.0 dBm	dBc	-42	-45	
Distortion						

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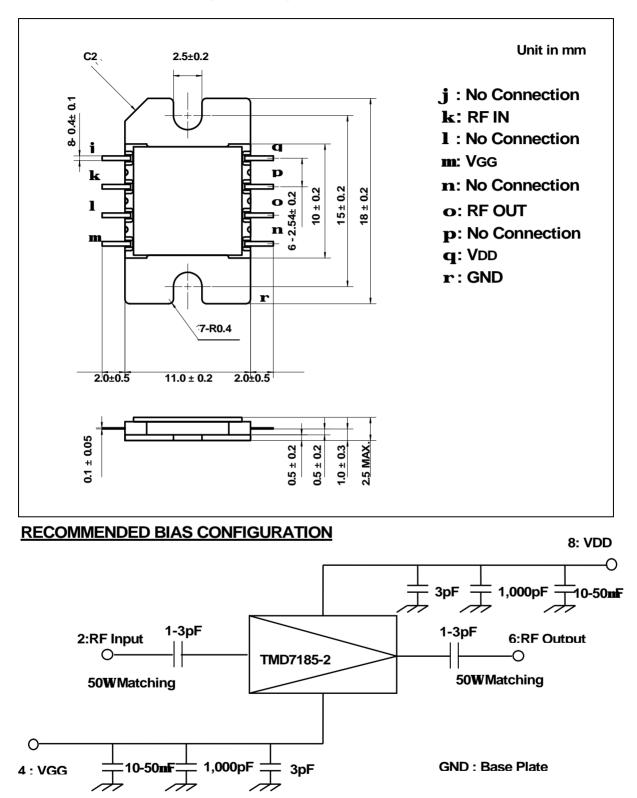
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

TOSHIBA CORPORATION

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TMD7185-2

### PACKAGE OUTLINE (2-11E1B)



#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.